

Notice of References Cited	Application/Control No. 10/519,724		Applicant(s)/Patent Under Reexamination LAERMER, FRANZ	
	Examiner RAKESH K. DHINGRA		Art Unit 1792	Page 1 of 1

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*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	A	US-5,741,396	04-1998	Loewenstein, Lee M.	438/724
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	L	US-			
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NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.